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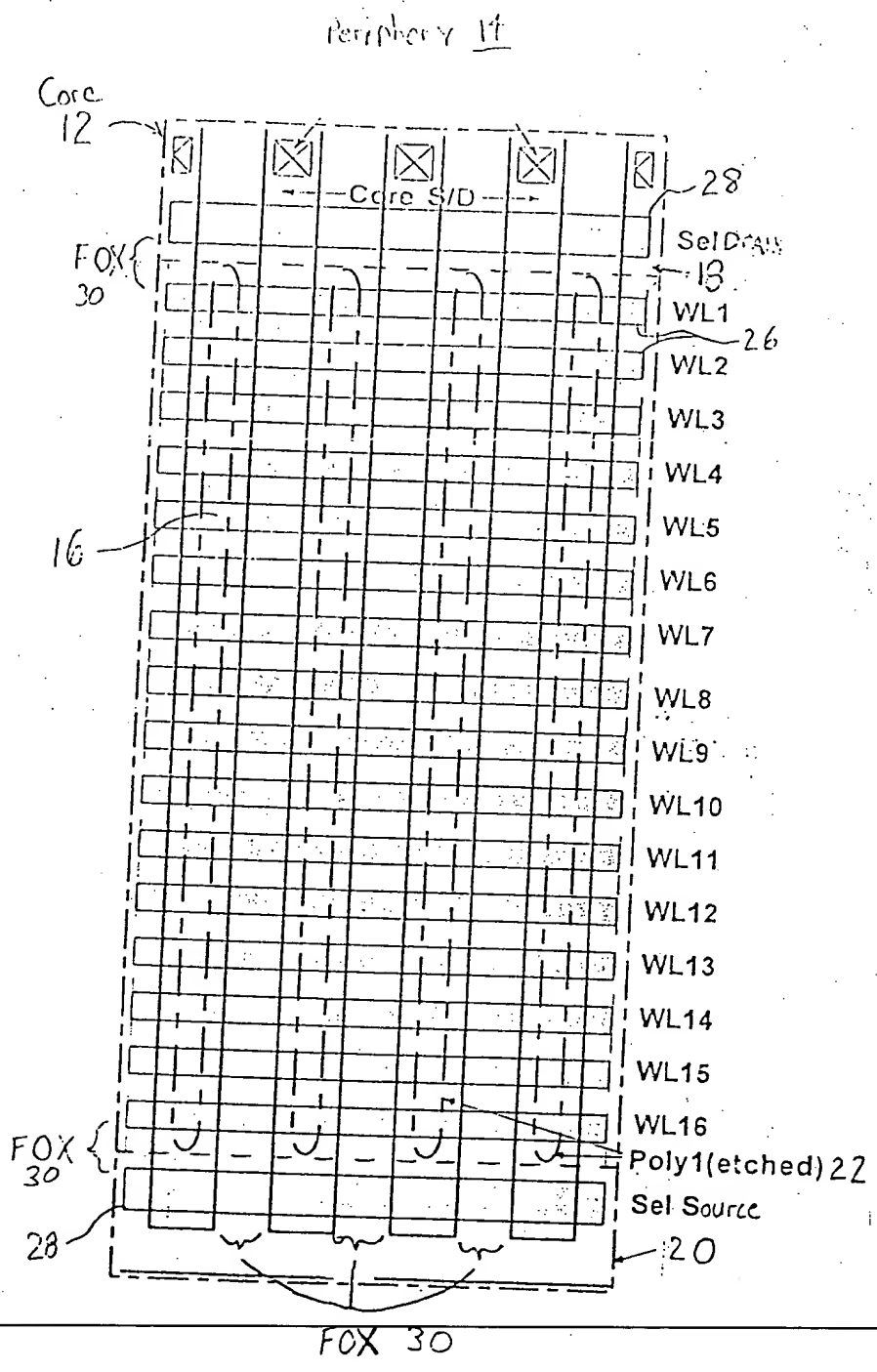
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Periphery 14

Figure 1
Prior Art

TOP SECRET

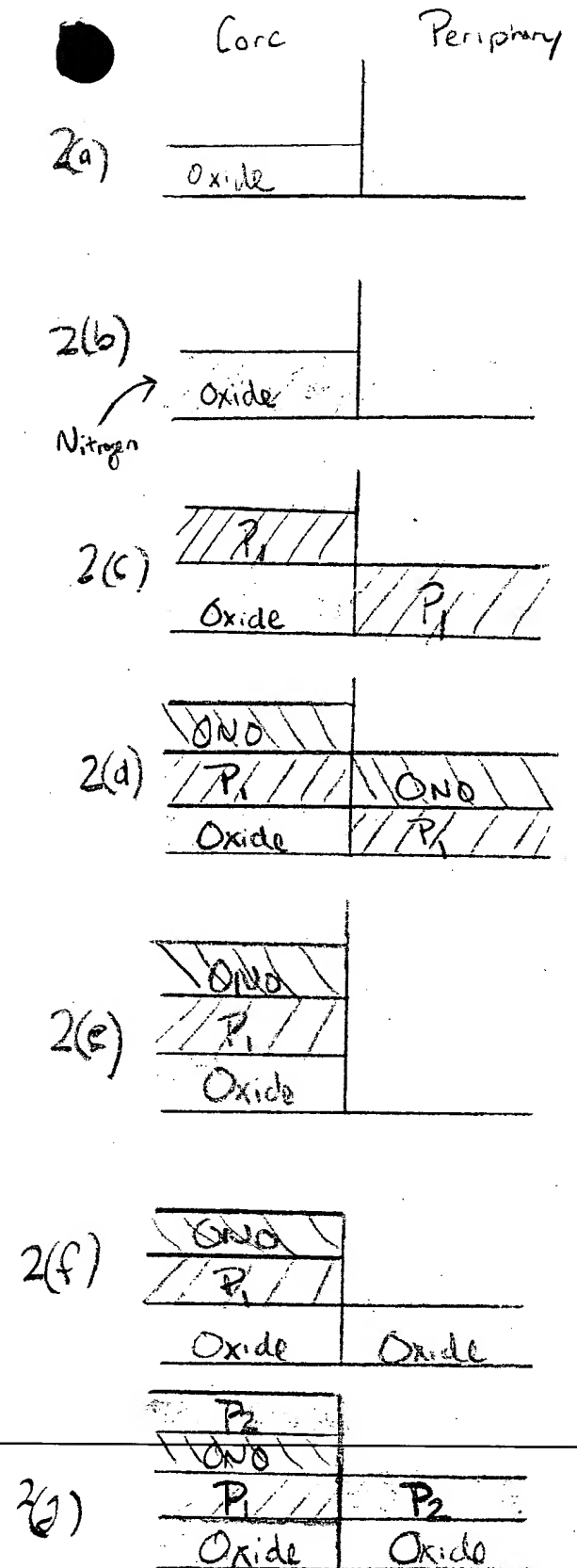
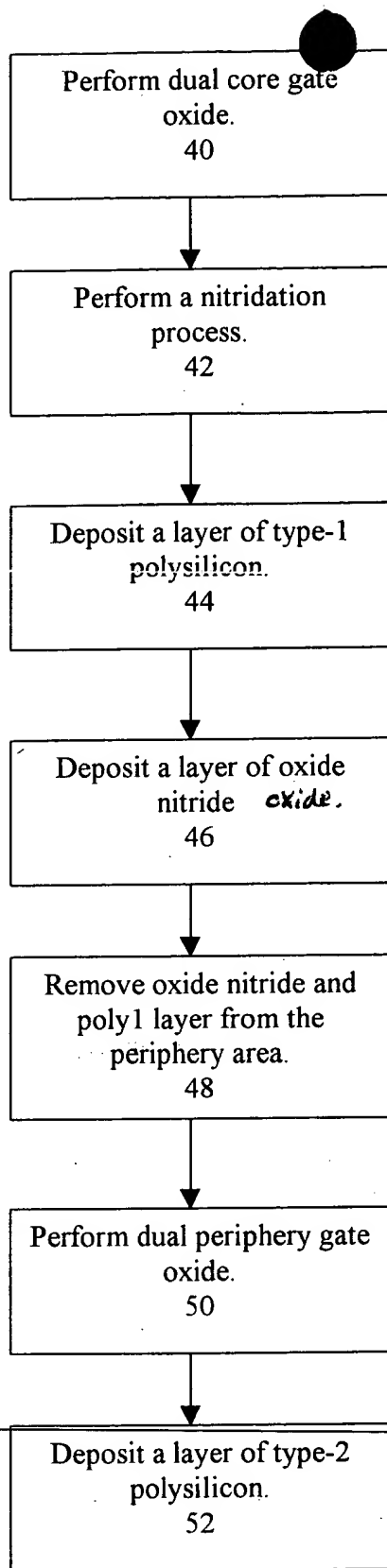


FIGURE 2
PRIOR ART

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graph TD; 200[Provide a portion of the dual periphery gate oxide. 200] --> 202[Provide a dual core gate oxide and complete the dual periphery gate oxide. 202]; 202 --> 204[Provide a nitridation process. 204]; 204 --> 206[Deposit a layer of type-1 polysilicon. 206]; 206 --> 208[Deposit a layer of oxide nitride. 208]; 208 --> 210[Remove oxide nitride and a portion of the poly1 layer from the periphery area. 210]; 210 --> 212[Deposit a layer of type-2 polysilicon. 212];
```

Provide a portion of the dual periphery gate oxide.
200

Provide a dual core gate oxide and complete the dual periphery gate oxide.
202

Provide a nitridation process.
204

Deposit a layer of type-1 polysilicon.
206

Deposit a layer of oxide nitride.
208

Remove oxide nitride and a portion of the poly1 layer from the periphery area.
210

Deposit a layer of type-2 polysilicon.
212

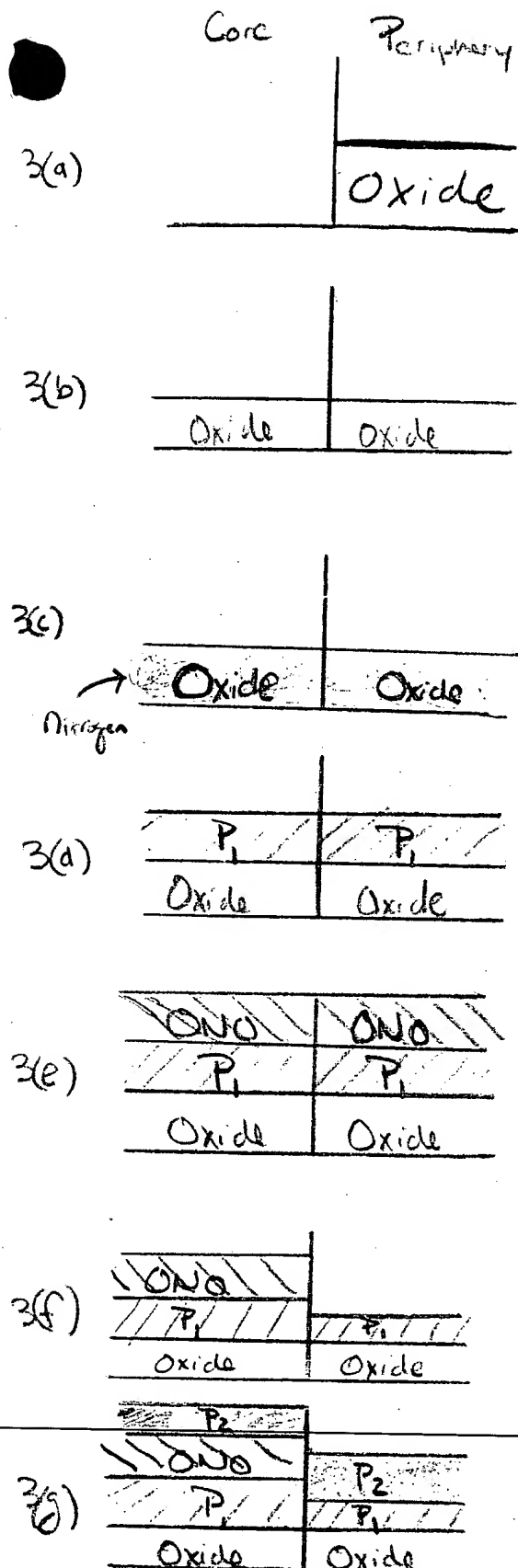


FIGURE 3

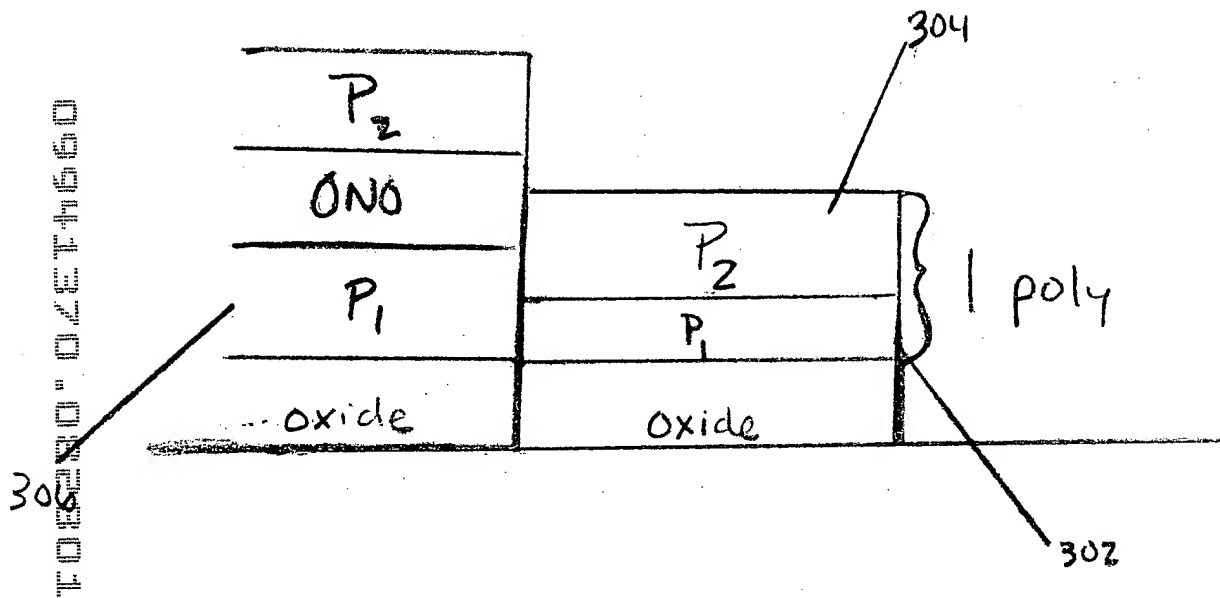


Figure 4